

MICROWAVE POWER GaAs FET

TIM1414-15L

MICROWAVE SEMICONDUCTOR TECHNICAL DATA

FEATURES

- ·BROAD BAND INTERNALLY MATCHED FET
- ·HIGH POWER

P1dB= 42.0dBm at 14.0GHz to 14.5GHz

·HIGH GAIN

G1dB= 6.0dB at 14.0GHz to 14.5GHz

LOW INTERMODULATION DISTORTION

IM3= -42dBc(Min.) at Pout= 30dBm (Single Carrier Level)

·HERMETICALLY SEALED PACKAGE



RF PERFORMANCE SPECIFICATIONS (Ta=25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Output Power at 1dB Gain Compression Point	P1dB	VDS= 9V IDSset= 4.0A f= 14.0 to 14.5GHz	dBm	41.0	42.0	_
Power Gain at 1dB Gain Compression Point	G1dB		dB	5.0	6.0	_
Drain Current	IDS1		Α		4.5	5.5
Gain Flatness	ΔG		dB	_	_	±0.8
Power Added Efficiency	ηadd		%	_	29	_
3rd Order Intermodulation Distortion	IM3	Two-Tone Test Po= 30dBm, ∆f= 5MHz (Single Carrier Level)	dBc	-42	-45	_
Drain Current	IDS2		Α	_	4.5	5.5
Channel Temperature Rise	∆Tch	(VDS × IDS + Pin – P1dB) × Rth(c-c)	°C	_	_	100

Recommended Gate Resistance(Rg): 100 Ω

ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Transconductance	gm	VDS= 3V IDS= 4.8A	S	_	3.0	_
Pinch-off Voltage	VGSoff	VDS= 3V IDS= 145mA	V	-1.5	-3.0	-4.5
Saturated Drain Current	IDSS	VDS= 3V VGS= 0V	Α	_	10.0	_
Gate-Source Breakdown Voltage	VGSO	IGS= -145 _μ A	V	-5		_
Thermal Resistance	Rth(c-c)	Channel to Case	°C/W		2.0	2.5

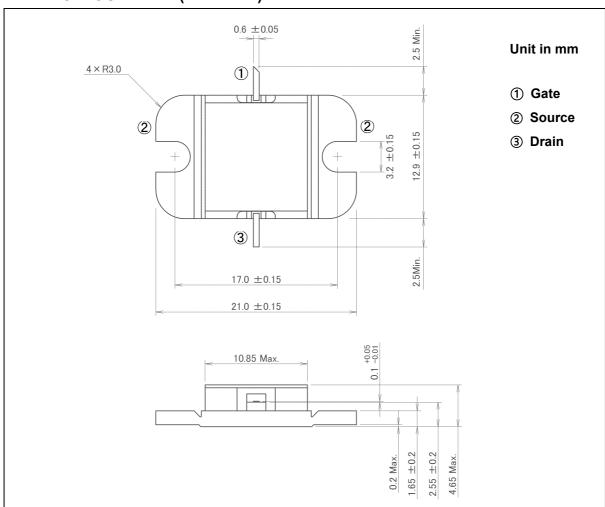
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ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain-Source Voltage	VDS	V	15
Gate-Source Voltage	VGS	V	-5
Drain Current	IDS	А	11.5
Total Power Dissipation (Tc= 25°C)	PT	W	60
Channel Temperature	Tch	°C	175
Storage	Tstg	°C	-65 to +175

PACKAGE OUTLINE (2-11C1B)



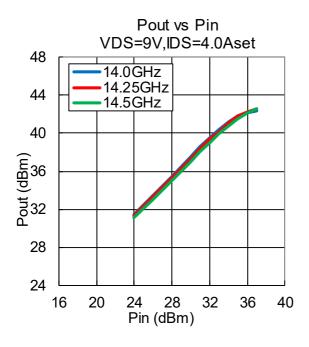
HANDLING PRECAUTIONS FOR PACKAGE MODEL

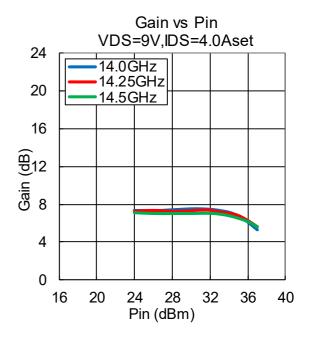
Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C or 3 seconds at 350°C.

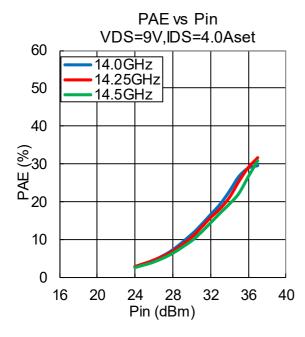
TYPICAL RF PERFORMANCE

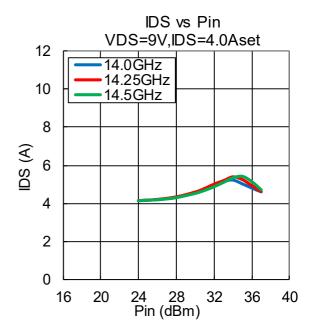
·Pout, Gain, PAE, IDS vs. Pin

VDS= 9 V, IDSset= 4.0 A, f= 14.0, 14.25, 14.5 GHz, Ta= +25 °C



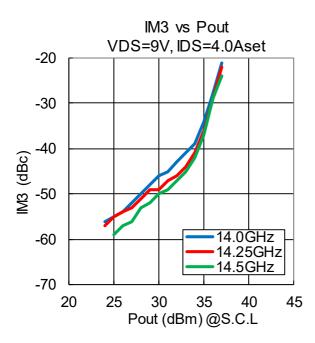






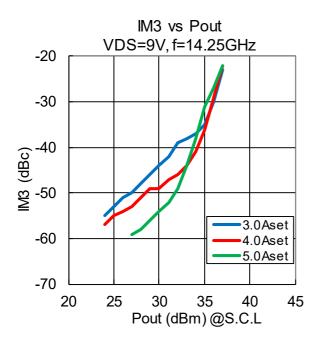
-IM3 vs. Pout

VDS= 9 V, IDSset= 4.0 A, f= 14.0, 14.25, 14.5 GHz, Δ f= 5 MHz , Ta= +25 $^{\circ}$ C



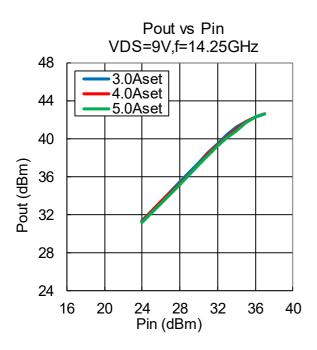
·IM3 vs. Pout

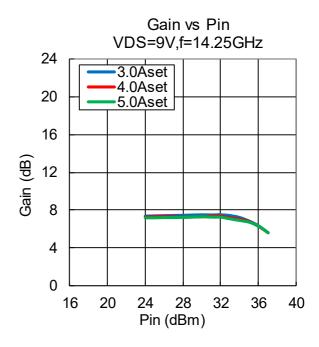
VDS= 9 V, IDSset= 3.0A, 4.0 A, 5.0A , f= 14.25GHz, Δ f= 5 MHz , Ta= +25 $^{\circ}$ C

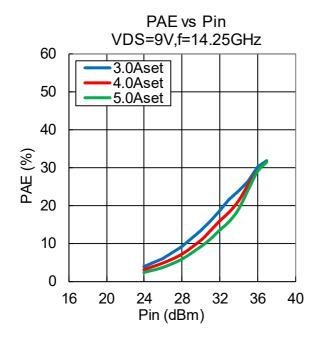


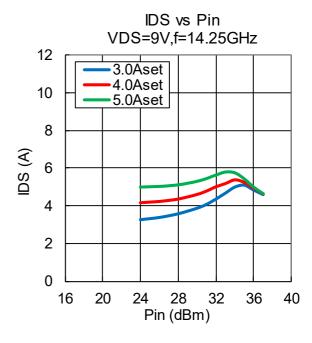
·Pout , Gain , PAE , IDS vs. Pin vs. IDSset

VDS= 9V, IDSset= 3.0, 4.0, 5.0 A, f= 14.25 GHz, Ta= +25 °C





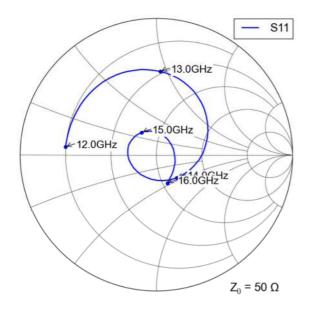


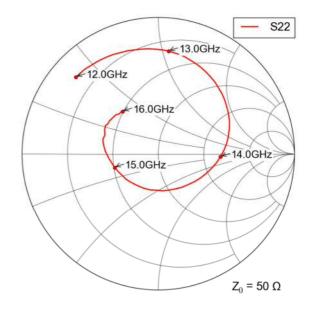


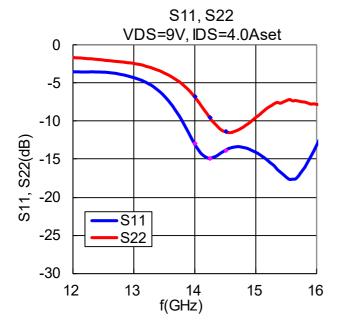


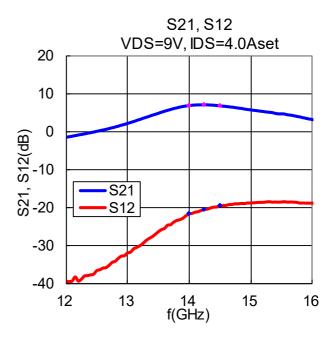
·S-Parameters

VDS= 9 V, IDSset= 4.0 A, f= 12.0 to 16.0 GHz, Ta= +25 $^{\circ}$ C











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